

## SM6016NSU-VB Datasheet

### N-Channel 60-V (D-S) MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>
60	0.025 at $V_{GS} = 10$ V	45
	0.030 at $V_{GS} = 4.5$ V	40

#### FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature



Available  
**RoHS\***  
 COMPLIANT



Drain Connected to Tab



N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$T_C = 25$ °C	$I_D$	45	A
	$T_C = 100$ °C		35	
Pulsed Drain Current		$I_{DM}$	100	
Continuous Source Current (Diode Conduction)		$I_S$	23	
Avalanche Current		$I_{AS}$	20	
Single Avalanche Energy (Duty Cycle $\leq 1$ %)	$L = 0.1$ mH	$E_{AS}$	20	mJ
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	100	W
	$T_A = 25$ °C		3 <sup>a</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	18	22	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		$R_{thJC}$	3.2	4	

Notes:

a. Surface Mounted on 1" x 1" FR4 board,  $t \leq 10$  sec.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0	2.0	3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.025		$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.055		
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.069		
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		0.030		
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		20		S
Dynamic <sup>a</sup>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		1500		pF
Output Capacitance	$C_{oss}$			140		
Reverse Transfer Capacitance	$C_{rss}$			60		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 23\text{ A}$		11	17	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			3		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			3		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 1.3\text{ }\Omega$ $I_D \cong 23\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		8	15	ns
Rise Time <sup>c</sup>	$t_r$			15	25	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			30	45	
Fall Time <sup>c</sup>	$t_f$			25	40	
Source-Drain Diode Ratings and Characteristics ( $T_C = 25\text{ }^{\circ}\text{C}$ )						
Pulsed Current	$I_{SM}$				50	A
Diode Forward Voltage	$V_{SD}$	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	60	ns

Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C unless noted**Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

**TYPICAL CHARACTERISTICS** 25 °C unless noted



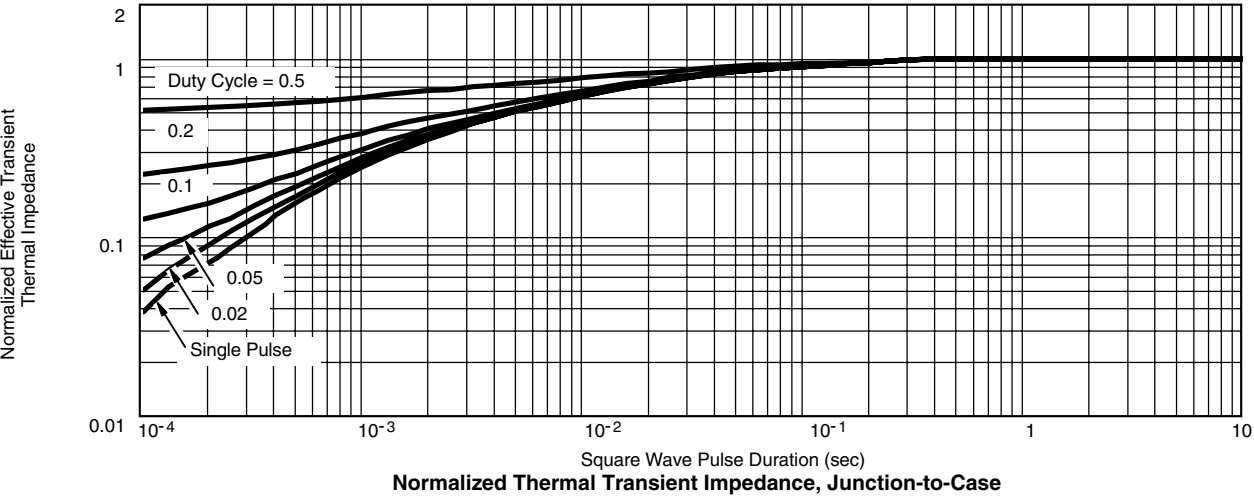
**THERMAL RATINGS**



**Maximum Drain Current  
vs. Ambient Temperature**

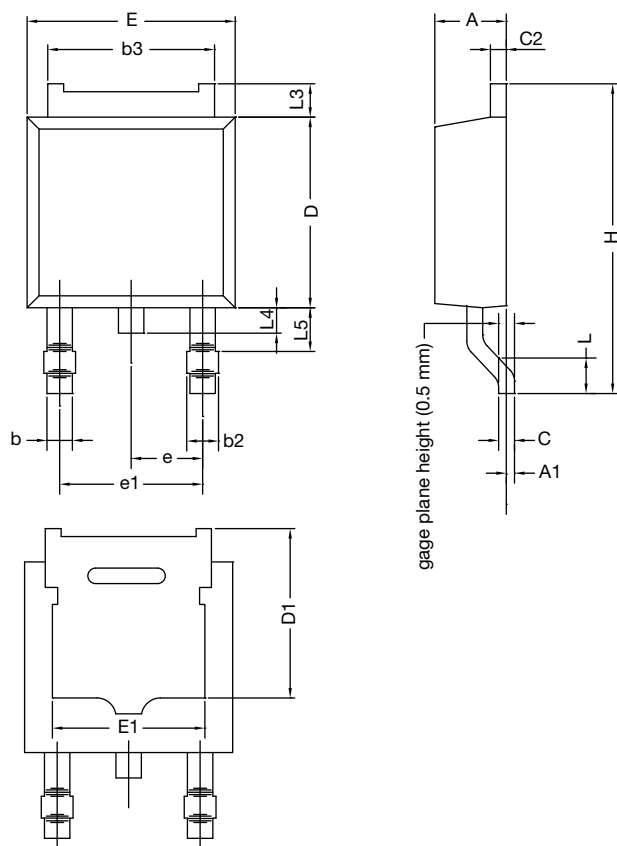


**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Case**

## TO-252AA CASE OUTLINE



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12				
DWG: 5347				

### Note

- Dimension L3 is for reference only.

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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